### SN65C1406, SN75C1406 TRIPLE LOW-POWER DRIVERS/RECEIVERS

SLLS148E - MAY 1990 - REVISED OCTOBER 2001

- Meet or Exceed the Requirements of TIA/EIA-232-F and ITU Recommendation V.28
- Very Low Power Consumption . . .5 mW Typ
- Wide Driver Supply Voltage Range . . . ±4.5 V to ±15 V
- Driver Output Slew Rate Limited to 30 V/μs Max
- Receiver Input Hysteresis . . . 1000 mV Typ
- Push-Pull Receiver Outputs
- On-Chip Receiver 1-μs Noise Filter
- Functionally Interchangeable With Motorola MC145406 and Texas Instruments TL145406
- Package Options Include Plastic Small-Outline (D, DW, NS) Packages and DIPs (N)

#### SN65C1406 . . . D PACKAGE SN75C1406 . . . D, DW, N, OR NS PACKAGE (TOP VIEW) V<sub>DD</sub> L 16 VCC 1RA **∏** 2 15**∏** 1RY 1DY **∏** 3 14**∏** 1DA 2RA 🛮 4 13 2RY 2DY 🛮 5 12 **□** 2DA 11 3RY 3RA **∏** 6 10**∏** 3DA 3DY **[**] 7 9 GND V<sub>SS</sub> 🛛 8

#### description

The SN65C1406 and SN75C1406 are low-power BiMOS devices containing three independent drivers and receivers that are used to interface data terminal equipment (DTE) with data circuit-terminating equipment (DCE). These devices are designed to conform to TIA/EIA-232-F. The drivers and receivers of the SN65C1406 and SN75C1406 are similar to those of the SN75C188 quadruple driver and SN75C189A quadruple receiver, respectively. The drivers have a controlled output slew rate that is limited to a maximum of 30 V/ $\mu$ s, and the receivers have filters that reject input noise pulses shorter than 1  $\mu$ s. Both these features eliminate the need for external components.

The SN65C1406 and SN75C1406 are designed using low-power techniques in a BiMOS technology. In most applications, the receivers contained in these devices interface to single inputs of peripheral devices such as ACEs, UARTs, or microprocessors. By using sampling, such peripheral devices are usually insensitive to the transition times of the input signals. If this is not the case, or for other uses, it is recommended that the SN65C1406 and SN75C1406 receiver outputs be buffered by single Schmitt input gates or single gates of the HCMOS, ALS, or 74F logic families.

The SN65C1406 is characterized for operation from  $-40^{\circ}$ C to  $85^{\circ}$ C. The SN75C1406 is characterized for operation from  $0^{\circ}$ C to  $70^{\circ}$ C.

#### AVAILABLE OPTIONS

		PACKAGED DEVICES							
TA	SMALL OUTLINE (D)	SMALL OUTLINE (DW)	PLASTIC DIP (N)	PLASTIC SMALL OUTLINE (NS)					
-40°C to 85°C	SN65C1406D								
0°C to 70°C	SN75C1406D	SN75C1406DW	SN75C1406N	SN75C1406NS					

The D, DW, and PW packages are available taped and reeled. Add the suffix R to device type (e.g., SN75C1406DR).



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



SLLS148E - MAY 1990 - REVISED OCTOBER 2001

## logic diagram (positive logic)

Typical of Each Receiver

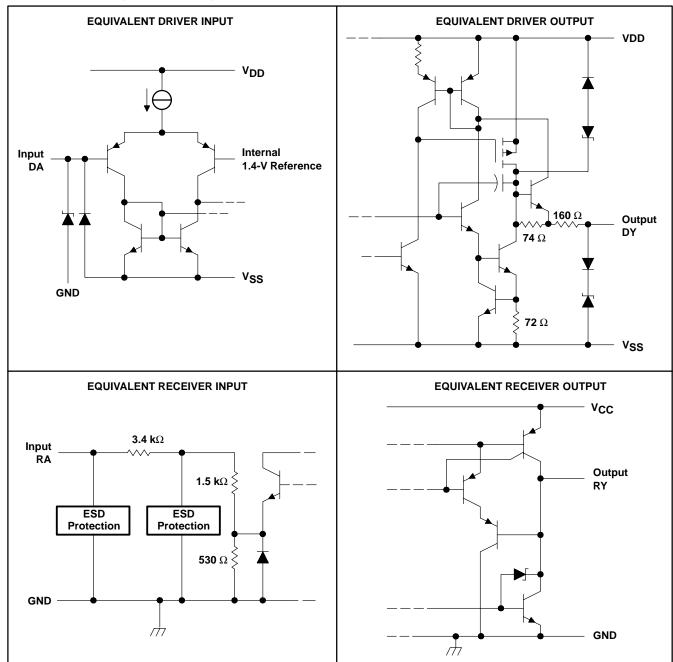


**Typical of Each Driver** 





### schematics of inputs and outputs



All resistor values shown are nominal.

## SN65C1406, SN75C1406 TRIPLE LOW-POWER DRIVERS/RECEIVERS

SLLS148E - MAY 1990 - REVISED OCTOBER 2001

absolute maximum ratings over operating	free-air temperature ra	ange (unless otherwise noted)†
Supply voltage: V <sub>DD</sub> (see Note 1)		
V <sub>SS</sub>		
V <sub>CC</sub>		
Input voltage range, V <sub>I</sub> : Driver		
Receiver		
Output voltage range, VO: Driver		$(V_{SS} - 6 \text{ V})$ to $(V_{DD} + 6 \text{ V})$
Receiver		$-0.3 \text{ V to } (V_{CC} + 0.3 \text{ V})$
Package thermal impedance, $\theta_{JA}$ (see Note	2): D package	
	DW package	57°C/W
	N package	67°C/W
	NS package	64°C/W
Lead temperature 1,6 mm (1/16 inch) from c	ase for 10 seconds	260°C
Storage temperature range, T <sub>stg</sub>		

#### recommended operating conditions

			MIN	NOM	MAX	UNIT	
$V_{DD}$	Supply voltage	4.5	12	15	V		
VSS	Supply voltage		-4.5	-12	-15	V	
Vcc	Supply voltage		4.5	5	6	V	
Vi	Input voltage	Driver	V <sub>SS</sub> +2		$V_{DD}$	V	
٧١	input voltage	Receiver			±25	V	
VIH	H High-level input voltage					V	
VIL	Low-level input voltage				0.8	V	
IOH	High-level output current				-1	mA	
loL	DL Low-level output curren				3.2	mA	
т.	Operating free-air temperature	SN65C1406	-40		85	°C	
Тд	SN75C1406				70	-0	



<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to the network ground terminal.

<sup>2.</sup> The package thermal impedance is calculated in accordance with JESD 51-7.

#### **DRIVER SECTION**

# electrical characteristics over operating free-air temperature range, $V_{DD}$ = 12 V, $V_{SS}$ = -12 V, $V_{CC}$ = 5 V $\pm$ 10% (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS		MIN	TYP <sup>†</sup>	MAX	UNIT
\/ <b>-</b>	Lligh lovel output voltage	V <sub>IH</sub> = 0.8 V,	$R_L = 3 k\Omega$ ,	$V_{DD} = 5 V$	V <sub>SS</sub> = -5 V	4	4.5		V
VOH	High-level output voltage	See Figure 1		V <sub>DD</sub> = 12 V,	V <sub>SS</sub> = -12 V	10	10.8		V
Vai	Low-level output voltage	V <sub>IH</sub> = 2 V,	$H = 2 \text{ V}, \qquad R_L = 3 \text{ k}\Omega,$		$V_{SS} = -5 V$		-4.4	-4	V
VOL	(see Note 3)	See Figure 1		$V_{DD} = 12 V$ ,	$V_{SS} = -12 \text{ V}$		-10.7	-10	V
lН	High-level input current	V <sub>I</sub> = 5 V,	See Figure 2					1	μΑ
IլL	Low-level input current	$V_{I} = 0$ ,	See Figure 2					-1	μΑ
los(H)	High-level short-circuit output current <sup>‡</sup>	V <sub>I</sub> = 0.8 V,	$V_O = 0$ or $V_{SS}$ ,	See Figure 1		-7.5	-12	-19.5	mA
los(L)	Low-level short-circuit output current <sup>‡</sup>	V <sub>I</sub> = 2 V,	$V_O = 0$ or $V_{DD}$ ,	See Figure 1		7.5	12	19.5	mA
	Supply current from VDD	No load,		$V_{DD} = 5 V$ ,	$V_{SS} = -5 V$		115	250	^
lDD	Supply current from VDD	All inputs at 2	V or 0.8 V	$V_{DD} = 12 V$ ,	$V_{SS} = -12 \text{ V}$		115	250	μΑ
laa	Supply ourrant from \/aa	No load,		$V_{DD} = 5 V$ ,	$V_{SS} = -5 V$		-115	-250	^
ISS	Supply current from VSS	All inputs at 2	V or 0.8 V	$V_{DD} = 12 V$ ,	$V_{SS} = -12 \text{ V}$		-115	-250	μΑ
rO	Output resistance	V <sub>DD</sub> = V <sub>SS</sub> = See Note 4	V <sub>CC</sub> = 0,	$V_0 = -2 \text{ V to}$	2 V,	300	400		Ω

<sup>&</sup>lt;sup>†</sup> All typical values are at  $T_A = 25$ °C.

NOTES: 3. The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only.

4. Test conditions are those specified by TIA/EIA-232-F.

## switching characteristics at $T_A$ = 25°C, $V_{DD}$ = 12 V, $V_{SS}$ = –12 V, $V_{CC}$ = 5 V $\pm$ 10%

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
tPLH	Propagation delay time, low- to high-level output§	$R_L$ = 3 kΩ to 7 kΩ, $C_L$ = 15 pF, See Figure 3		1.2	3	μs
tPHL	Propagation delay time, high- to low-level output§	$R_L$ = 3 kΩ to 7 kΩ, $C_L$ = 15 pF, See Figure 3		2.5	3.5	μs
tTLH	Transition time, low- to high-level output¶	$R_L$ = 3 kΩ to 7 kΩ, $C_L$ = 15 pF, See Figure 3	0.53	2	3.2	μs
tTHL	Transition time, high- to low-level output¶	R <sub>L</sub> = 3 k $\Omega$ to 7 k $\Omega$ , C <sub>L</sub> = 15 pF, See Figure 3	0.53	2	3.2	μs
tTLH	Transition time, low- to high-level output#	R <sub>L</sub> = 3 k $\Omega$ to 7 k $\Omega$ , C <sub>L</sub> = 2500 pF, See Figure 3		1	2	μs
tTHL	Transition time, high- to low-level output#	$R_L$ = 3 kΩ to 7 kΩ, $C_L$ = 2500 pF, See Figure 3		1	2	μs
SR	Output slew rate	R <sub>L</sub> = 3 kΩ to 7 kΩ, C <sub>L</sub> = 15 pF, See Figure 3	4	10	30	V/μs

<sup>\$</sup> tPHL and tPLH include the additional time due to on-chip slew rate and are measured at the 50% points.



<sup>‡</sup> Not more than one output should be shorted at a time.

Measured between 10% and 90% points of output waveform

<sup>#</sup> Measured between 3-V and -3-V points of output waveform (TIA/EIA-232-F conditions) with all unused inputs tied either high or low

#### RECEIVER SECTION

# electrical characteristics over operating free-air temperature range, $V_{DD}$ = 12 V, $V_{SS}$ = -12 V, $V_{CC}$ = 5 V $\pm$ 10% (unless otherwise noted)

	PARAMETER		TEST CO	NDITIONS	MIN	TYP†	MAX	UNIT
VIT+	Positive-going input threshold voltage	See Figure 5	See Figure 5					V
V <sub>IT</sub> _	Negative-going input threshold voltage	See Figure 5	See Figure 5					V
V <sub>hys</sub>	Input hysteresis voltage (V <sub>IT+</sub> -V <sub>IT-</sub> )				600	1000		mV
		$V_I = 0.75 \text{ V}, \qquad I_{OH} = -20 \mu\text{A},$		See Figure 5 and Note 5	3.5			
VOH High-level output voltage	.,		V <sub>CC</sub> = 4.5 V	2.8	4.4		v I	
VOH	riigii-level output voltage	V <sub>I</sub> = 0.75 V, See Figure 5	$I_{OH} = -1 \text{ mA},$	V <sub>CC</sub> = 5 V	3.8	4.9		ľ
		Gee rigule o		V <sub>CC</sub> = 5.5 V	4.3	5.4		
VOL	Low-level output voltage	V <sub>I</sub> = 3 V,	$I_{OL} = 3.2 \text{ mA},$	See Figure 5		0.17	0.4	V
I	High-level input current	V <sub>I</sub> = 2.5 V	3.6	4.6	8.3	m 1		
ΊΗ	nign-level input current	V <sub>I</sub> = 3 V	0.43	0.55	1	mA		
1	Low-level input current	$V_{I} = -2.5 V$	-3.6	<b>–</b> 5	-8.3	mA		
lIL.	Low-level input current	$V_{I} = -3 V$	-0.43	-0.55	-1	ША		
los(H)	High-level short-circuit output current	V <sub>I</sub> = 0.75 V,	$V_{O} = 0$ ,	See Figure 4		-8	-15	mA
IOS(L)	Low-level short-circuit output current	VI = VCC,	$V_O = V_{CC}$	See Figure 4		13	25	mA
loo	Supply current from V <sub>CC</sub>	No load, All inputs at 0 or 5 V		$V_{DD} = 5 \text{ V},  V_{SS} = -5 \text{ V}$		320	450	
Icc	Supply carrent none vCC			$V_{DD} = 12 \text{ V},  V_{SS} = -12 \text{ V}$		320	450	μA

<sup>&</sup>lt;sup>†</sup> All typical values are at  $T_A = 25$ °C.

NOTE 5: If the inputs are left unconnected, the receiver interprets this as an input low and the receiver outputs remain in the high state.

## switching characteristics at $T_A$ = 25°C, $V_{DD}$ = 12 V, $V_{SS}$ = -12 V, $V_{CC}$ = 5 V $\pm$ 10% (unless otherwise noted)

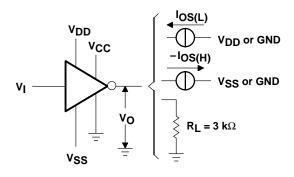
	PARAMETER	TEST CO	NDITIONS	MIN	TYP	MAX	UNIT
tPLH	Propagation delay time, low- to high-level output	C <sub>L</sub> = 50 pF, See Figure 6	$R_L = 5 k\Omega$ ,		3	4	μs
<sup>t</sup> PHL	Propagation delay time, high- to low-level output	C <sub>L</sub> = 50 pF, See Figure 6	$R_L = 5 k\Omega$ ,		3	4	μs
tTLH	Transition time, low- to high-level output <sup>‡</sup>	C <sub>L</sub> = 50 pF, See Figure 6	$R_L = 5 \text{ k}\Omega$ ,		300	450	ns
tTHL	Transition time, high- to low-level output <sup>‡</sup>	C <sub>L</sub> = 50 pF, See Figure 6	$R_L = 5 \text{ k}\Omega$ ,		100	300	ns
t <sub>w</sub> (N)	Duration of longest pulse rejected as noise§	$C_L = 50 pF$ ,	R <sub>L</sub> = 5 kΩ	1		4	μs

<sup>&</sup>lt;sup>‡</sup> Measured between 10% and 90% points of output waveform



<sup>§</sup> The receiver ignores any positive- or negative-going pulse that is less than the minimum value of  $t_{W(N)}$  and accepts any positive- or negative-going pulse greater than the maximum of  $t_{W(N)}$ .

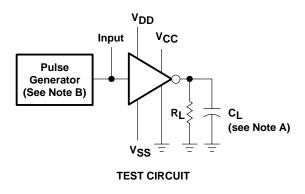
#### PARAMETER MEASUREMENT INFORMATION

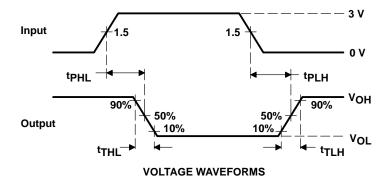


V<sub>I</sub> — V<sub>DD</sub> V<sub>CC</sub> V<sub>CC</sub> V<sub>SS</sub>

Figure 1. Driver Test Circuit V<sub>OH</sub>, V<sub>OL</sub>, I<sub>OS(L)</sub>, I<sub>OS(H)</sub>

Figure 2. Driver Test Circuit, I<sub>IL</sub>, I<sub>IH</sub>

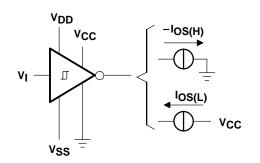




NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics:  $t_W$  = 25  $\mu$ s, PRR = 20 kHz,  $Z_O$  = 50  $\Omega$ ,  $t_f$  =  $t_f$  < 50 ns.

Figure 3. Driver Test Circuit and Voltage Waveforms



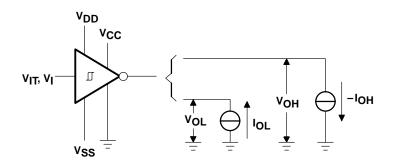
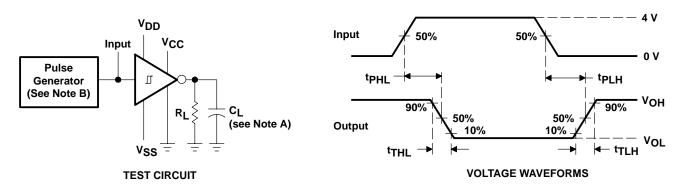


Figure 4. Receiver Test Circuit, IOS(H), IOS(L)

Figure 5. Receiver Test Circuit,  $V_{IT}$ ,  $V_{OL}$ ,  $V_{OH}$ 

SLLS148E - MAY 1990 - REVISED OCTOBER 2001

#### PARAMETER MEASUREMENT INFORMATION



NOTES: C. C<sub>I</sub> includes probe and jig capacitance.

D. The pulse generator has the following characteristics:  $t_W = 25 \mu s$ , PRR = 20 kHz,  $Z_Q = 50 \Omega$ ,  $t_f = t_f < 50 ns$ .

Figure 6. Receiver Test Circuit and Voltage Waveforms

#### **APPLICATION INFORMATION**

The TIA/EIA-232-F specification is for data interchange between a host computer and a peripheral at signaling rates up to 20 kbit/s. Many TIA/EIA-232-F devices will operate at higher data rates with lower capacitive loads (short cables). For reliable operation at greater than 20 kbit/s, the designer needs to have control of both ends of the cable. By mixing different types of TIA/EIA-232-F devices and cable lengths, errors can occur at higher frequencies (above 20 kbit/s). When operating within the TIA/EIA-232-F requirements of less than 20 kbit/s and with compliant line circuits, interoperability is assured. For applications operating above 20 kbit/s, the design engineer should consider devices and system designs that meet the TIA/EIA-232-F requirements.









#### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
SN65C1406D	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C1406DE4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C1406DG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C1406DR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C1406DRE4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C1406DRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C1406N	OBSOLETE	PDIP	N	16		TBD	Call TI	Call TI
SN75C1406D	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C1406DE4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C1406DG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C1406DR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C1406DRE4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C1406DRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C1406DW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C1406DWE4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C1406DWG4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C1406DWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C1406DWRE4	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C1406DWRG4	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C1406N	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
SN75C1406NE4	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
SN75C1406NSR	ACTIVE	so	NS	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C1406NSRE4	ACTIVE	SO	NS	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C1406NSRG4	ACTIVE	SO	NS	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

(1) The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.



#### PACKAGE OPTION ADDENDUM

4-Jun-2007

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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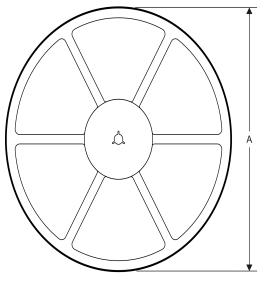
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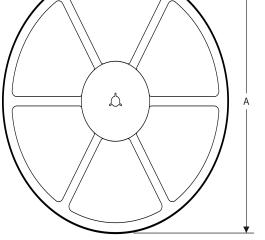
## PACKAGE MATERIALS INFORMATION

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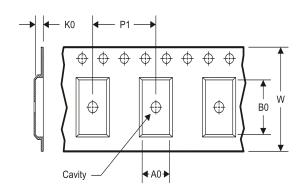
#### TAPE AND REEL INFORMATION

#### **REEL DIMENSIONS**





#### **TAPE DIMENSIONS**



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### TAPE AND REEL INFORMATION

### \*All dimensions are nominal

All differsions are nominal	All differsions are nominal											
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C1406DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN75C1406DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN75C1406DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
SN75C1406NSR	SO	NS	16	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1

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\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C1406DR	SOIC	D	16	2500	333.2	345.9	28.6
SN75C1406DR	SOIC	D	16	2500	333.2	345.9	28.6
SN75C1406DWR	SOIC	DW	16	2000	367.0	367.0	38.0
SN75C1406NSR	SO	NS	16	2000	367.0	367.0	38.0

## N (R-PDIP-T\*\*)

## PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



## D (R-PDS0-G16)

#### PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



## D (R-PDSO-G16)

## PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



DW (R-PDSO-G16)

## PLASTIC SMALL OUTLINE



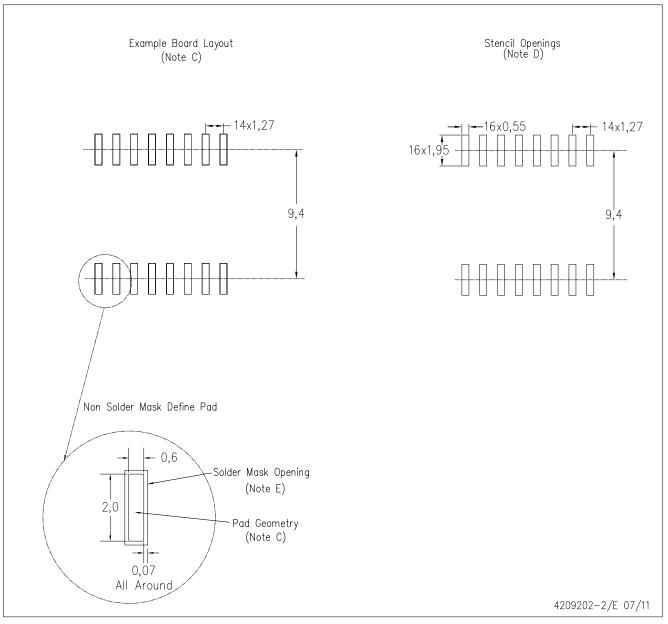
NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AA.



DW (R-PDSO-G16)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Refer to IPC7351 for alternate board design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC—7525
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



#### **MECHANICAL DATA**

## NS (R-PDSO-G\*\*)

## 14-PINS SHOWN

#### PLASTIC SMALL-OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



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